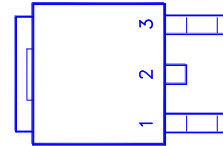
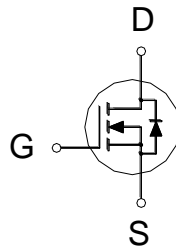




PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
60V	22.5mΩ	32A



- 1. GATE
- 2. DRAIN
- 3. SOURCE

ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ °C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	$T_C = 25\text{ °C}$	I_D	32	A
	$T_C = 100\text{ °C}$		20	
Pulsed Drain Current ¹		I_{DM}	100	
Avalanche Current		I_{AS}	26	
Avalanche Energy	$L = 0.1\text{mH}$	E_{AS}	33.8	mJ
Power Dissipation	$T_C = 25\text{ °C}$	P_D	50	W
	$T_C = 100\text{ °C}$		20	
Junction & Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		2.5	°C / W
Junction-to-Ambient	$R_{\theta JA}$		62.5	

¹Pulse width limited by maximum junction temperature.

ELECTRICAL CHARACTERISTICS ($T_J = 25\text{ °C}$, Unless Otherwise Noted)

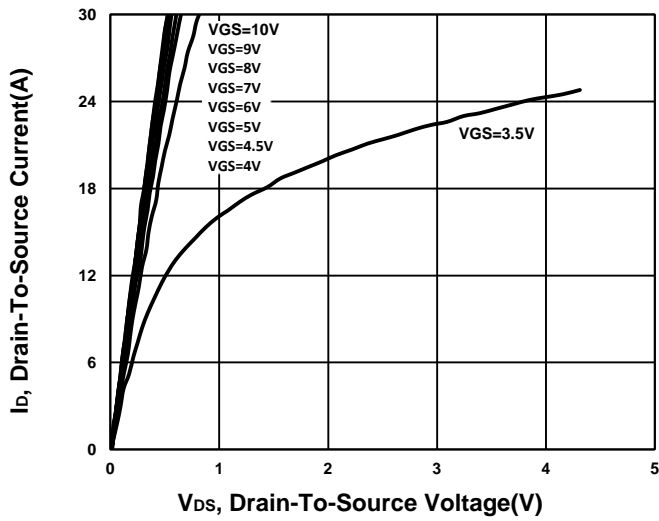
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	60			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.3	1.75	2.3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 48V, V_{GS} = 0V$			1	μA
		$V_{DS} = 40V, V_{GS} = 0V, T_J = 125\text{ °C}$			10	
Drain-Source On-State Resistance ₁	$R_{DS(ON)}$	$V_{GS} = 4.5V, I_D = 12A$		19	30	mΩ
		$V_{GS} = 10V, I_D = 20A$		17	22.5	

Forward Transconductance ¹	g_{fs}	$V_{DS} = 5V, I_D = 20A$		40		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$	812	1016	1219	pF
Output Capacitance	C_{oss}		100	125	150	
Reverse Transfer Capacitance	C_{rss}		48	81	113	
Gate Resistance	R_g	$V_{GS} = 0V, V_{DS} = 0V, f = 1MHz$	0.5	1	1.5	Ω
Total Gate Charge ²	$Q_{g(VGS=10V)}$	$V_{DS} = 30V, I_D = 20A$	18	23.2	28	nC
	$Q_{g(VGS=4.5V)}$		10.4	13	15.6	
Gate-Source Charge ²	Q_{gs}		2.6	3.2	3.8	
Gate-Drain Charge ²	Q_{gd}		4.4	7.4	10.4	
Turn-On Delay Time ²	$t_{d(on)}$		$V_{DS} = 30V$ $I_D \cong 20A, V_{GS} = 10V, R_{GEN} = 6\Omega$		38	
Rise Time ²	t_r			24		
Turn-Off Delay Time ²	$t_{d(off)}$			102		
Fall Time ²	t_f			35		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_J = 25^\circ C$)						
Continuous Current ³	I_S				32	A
Forward Voltage ¹	V_{SD}	$I_F = 20A, V_{GS} = 0V$			1.3	V
Reverse Recovery Time	t_{rr}	$I_F = 20A, di_F/dt = 100A / \mu S$	11	22	33	nS
Reverse Recovery Charge	Q_{rr}		7.5	15	22.5	nC

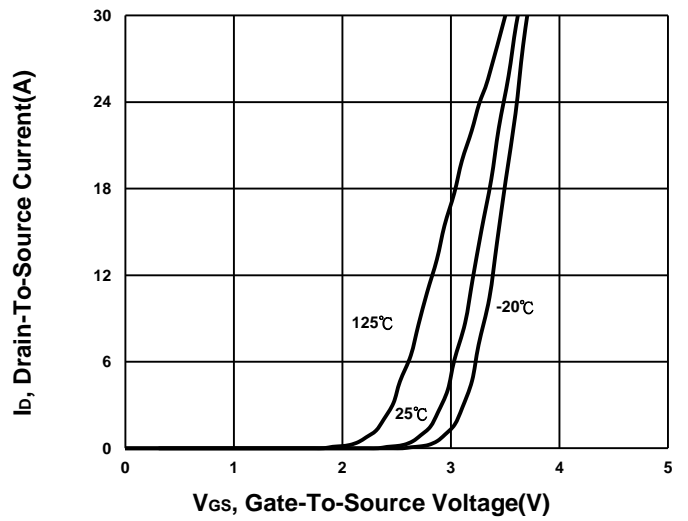
¹Pulse test : Pulse Width $\leq 300 \mu sec$, Duty Cycle $\leq 2\%$.

²Independent of operating temperature.

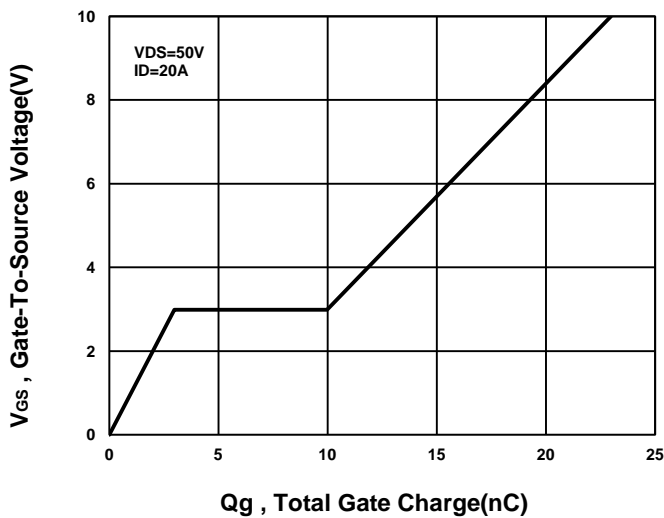
Output Characteristics



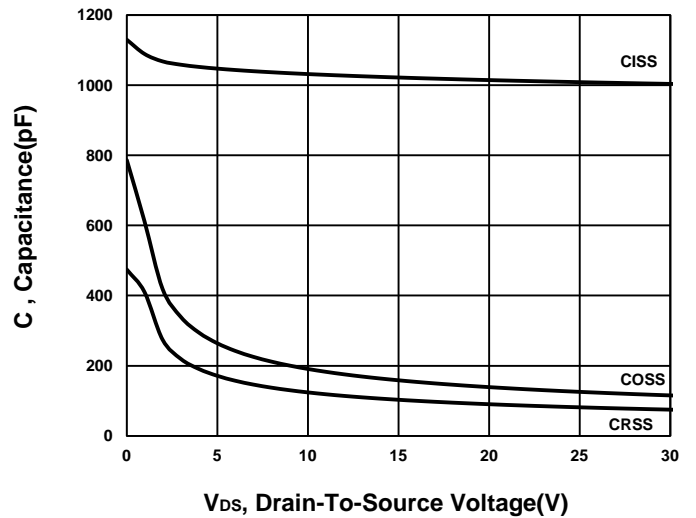
Transfer Characteristics



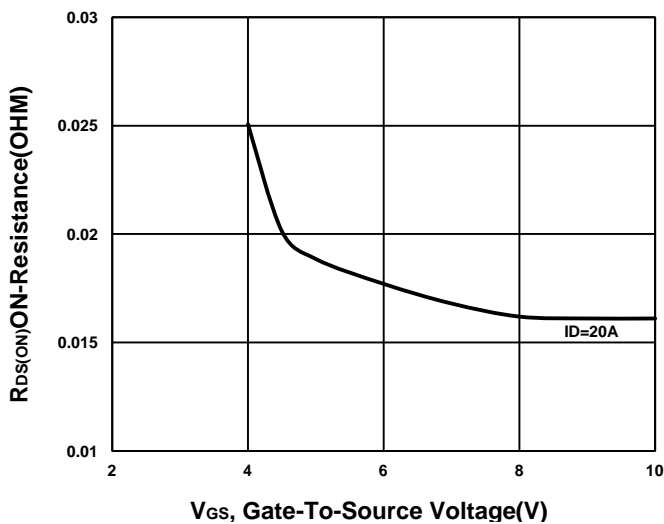
Gate charge Characteristics



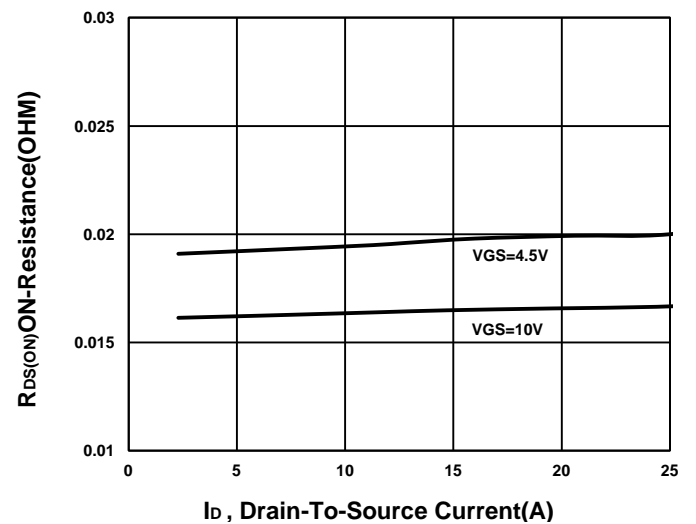
Capacitance Characteristic



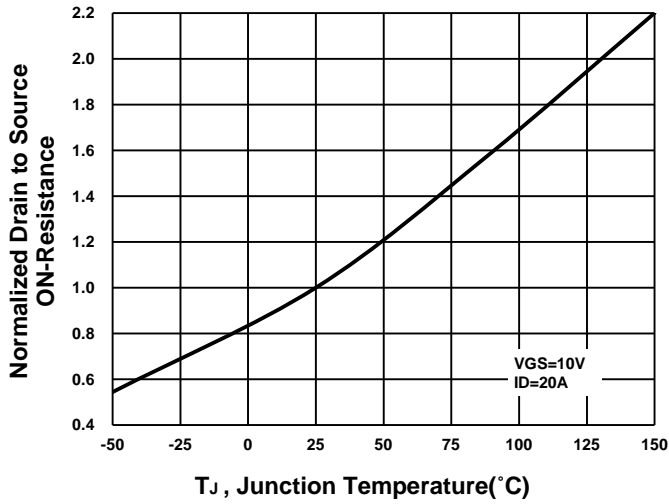
On-Resistance VS Gate-To-Source



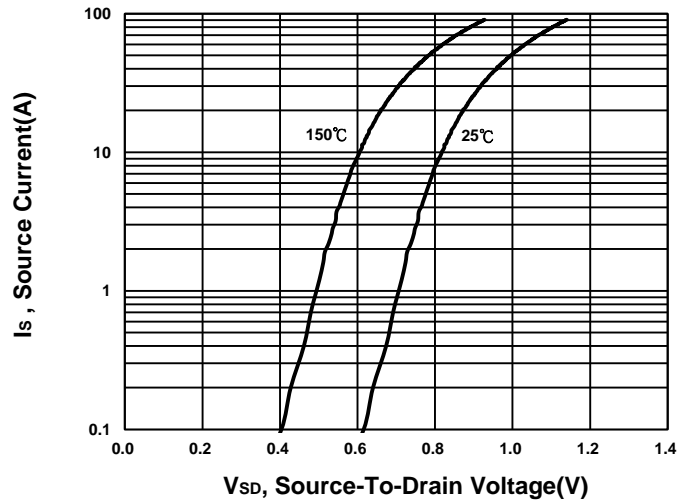
On-Resistance VS Drain Current



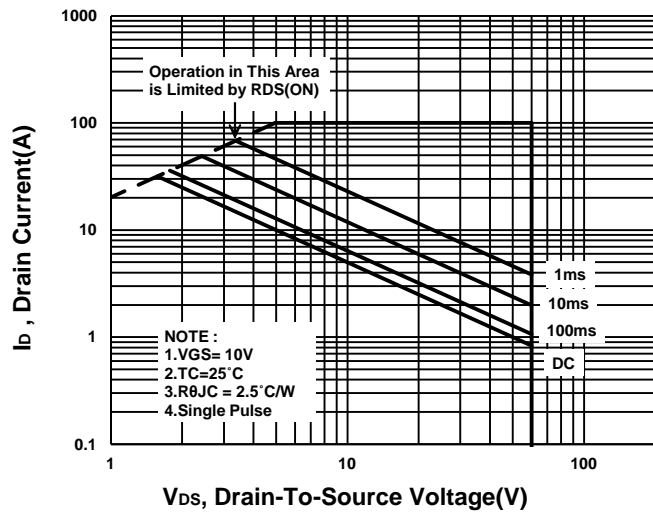
On-Resistance VS Temperature



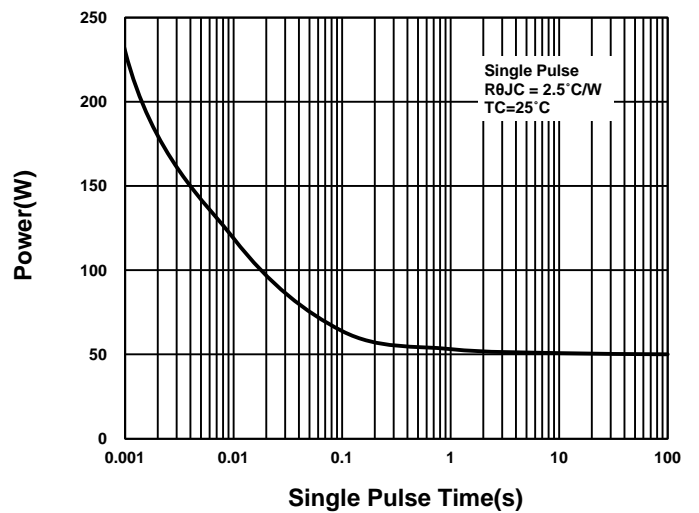
Source-Drain Diode Forward Voltage



Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve

